Amendments to the Claims:

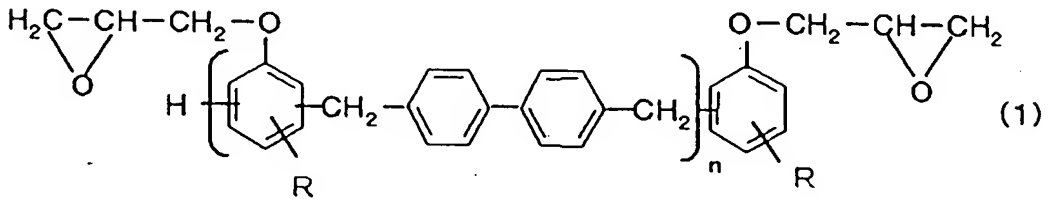
This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Please add new Claim 9.

1. (Original) A resin composition for encapsulating a semiconductor chip comprising:

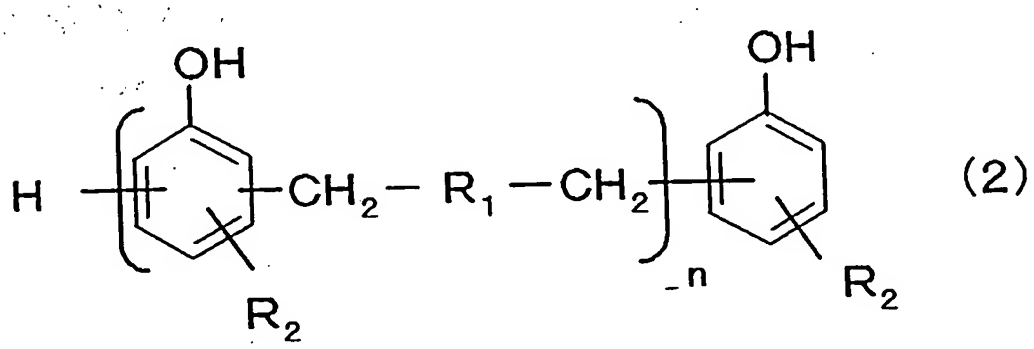
an epoxy resin (A) represented by general formula (1):



(1)

wherein R represents hydrogen or alkyl having up to four carbon atoms; and n is a positive number from 1 to 10 as an average;

a phenol resin (B) represented by general formula (2):



(2)

wherein R_1 represents phenylene or biphenylene; R_2 represents alkyl having up to four carbon atoms; and n is a positive number from 1 to 10 as an average;

an inorganic filler (C);

a curing accelerator (D);

a silane coupling agent (E); and

Compound (F) containing two and more hydroxyl groups combined with each of adjacent carbon atoms comprising an aromatic ring.

2. (Original) The resin composition for encapsulating a semiconductor chip according to Claim 1, wherein the resin composition comprises said Compound (F) in more than or equal to 0.01 wt%.

3. (Original) The resin composition for encapsulating a semiconductor chip according to Claim 1, wherein the resin composition comprises said silane coupling agent (E) in 0.01 wt% to 1 wt% both inclusive.

4. (Original) The resin composition for encapsulating a semiconductor chip according to Claim 1, wherein said compound (F) contains two hydroxyl groups combined with each of adjacent carbon atoms comprising said aromatic ring.

5. (Previously Presented) he resin composition for encapsulating a semiconductor chip according to Claim 1, wherein the aromatic ring is a naphthalene ring in Compound (F).

6. (Original) The resin composition for encapsulating a semiconductor chip according to Claim 5, wherein said Compound (F) contains two hydroxyl groups combined with each of adjacent carbon atoms comprising said naphthalene ring.

7. (Original) The resin composition for encapsulating a semiconductor chip according to Claims 1, wherein the resin composition comprises said inorganic filler (C) in 84 wt% to 90 wt% both inclusive.

8. (Previously Presented) A semiconductor device wherein a semiconductor chip is encapsulated by the resin composition according to Claim 1.

9. (New) The resin composition for encapsulating a semiconductor chip according to Claim 1,

wherein said inorganic filler (C) is present in an amount of 84 wt% to 90 wt% both inclusive,

said silane coupling agent (E) is present in an amount of 0.01 wt% to 1 wt% both inclusive, and

said Compound (F) is present in an amount of 0.01 wt% to 0.5 wt% both inclusive.